

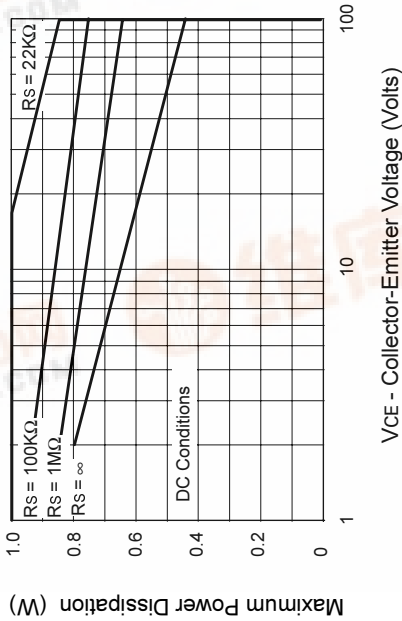


ZTX704 ZTX705

ELECTRICAL CHARACTERISTICS (at T_{amb} = 25°C).

PARAMETER	SYMBOL	ZTX704		ZTX705		UNIT	CONDITIONS.
		MIN.	MAX.	MIN.	MAX.		
Static Forward Current Transfer Ratio	h_{FE}	3K 3K 3K 2K	30K	3K 3K 3K 2K	30K		$I_C = -10mA, V_{CE} = -5V^*$ $I_C = -100mA, V_{CE} = -5V^*$ $I_C = -1A, V_{CE} = -5V^*$ $I_C = -2A, V_{CE} = -5V^*$
Transition Frequency	f_T	160 Typical		160 Typical		MHz	$I_C = -100mA, V_{CE} = -10V$ $f = 20MHz$
Input Capacitance	C_{ibo}	90 Typical		90 Typical		pF	$V_{EB} = -0.5V, f = 1MHz$
Output Capacitance	C_{obo}	15 Typical		15 Typical		pF	$V_{CE} = -10V, f = 1MHz$
Switching Times	t_{on}	0.6 Typical		0.6 Typical		μs	$I_C = -0.5A, V_{CE} = -10V$ $I_B = I_{B2} = -0.5mA$
	t_{off}	0.8 Typical		0.8 Typical		μs	

Measured under pulsed conditions. Pulse width=300 μs . Duty cycle $\leq 2\%$



Voltage Derating Graph

The maximum permissible operational temperature can be obtained from this graph using the following equation

$$T_{amb(max)} = \frac{Power(max) - Power(act)}{0.0057} + 25^{\circ}C$$

$T_{amb(max)}$ = Maximum operating ambient temperature
 $Power(max)$ = Maximum power dissipation figure, obtained from the above graph for a given V_{CE} and source resistance (R_S)
 $Power(actual)$ = Actual power dissipation in users circuit

PNP SILICON PLANAR MEDIUM POWER DARLINGTON TRANSISTORS

ISSUE 3 – MAY 94

FEATURES

- * 120 Volt V_{CEO}
 - * 1 Amp continuous current
 - * Gain of 3K at $I_C = 1$ Amp
 - * $P_{tot} = 1$ Watt
- APPLICATIONS
- * Lamp, solenoid and relay drivers

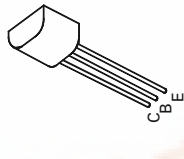
ABSOLUTE MAXIMUM RATINGS.

PARAMETER	SYMBOL	ZTX704	ZTX705	UNIT
Collector-Base Voltage	V_{CBO}	-120	-140	V
Collector-Emitter Voltage	V_{CEO}	-100	-120	V
Emitter-Base Voltage	V_{EBO}	-10	-10	V
Peak Pulse Current	I_{CM}	-4	-4	A
Continuous Collector Current	I_C	-1	-1	A
Power Dissipation at T _{amb} = 25°C derate above 25°C	P_{tot}	1	1	W
Operating and Storage Temperature Range	T_j, T_{stg}	-55 to +200		°C

ELECTRICAL CHARACTERISTICS (at T_{amb} = 25°C unless otherwise stated).

PARAMETER	SYMBOL	ZTX704		ZTX705		UNIT	CONDITIONS.
		MIN.	MAX.	MIN.	MAX.		
Collector-Base Breakdown Voltage	$V_{(BR)CBO}$	-120		-140		V	$I_C = 100\mu A$
Collector-Emitter Breakdown Voltage	$V_{CEO(SUS)}$	-100		-120		V	$I_C = 10mA^*$
Emitter-Base Breakdown Voltage	$V_{(BR)EBO}$	-10		-10		V	$I_E = 100\mu A$
Collector Cut-Off Current	I_{CBO}		-0.1		-0.1	μA	$V_{CB} = -100V$ $V_{CB} = -120V$ $V_{CB} = -100V, T_{amb} = 100^{\circ}C$ $V_{CB} = -120V, T_{amb} = 100^{\circ}C$
Collector Cut-Off Current	I_{CES}		-10		-10	μA	$V_{CES} = -80V$
Emitter Cut-Off Current	I_{EBO}		-0.1		-0.1	μA	$V_{EB} = -8V$
Collector-Emitter Saturation Voltage	$V_{CE(sat)}$	-1.3	-2.5	-1.3	-2.5	V	$I_C = 1A, I_B = 1mA^*$ $I_C = 2A, I_B = 2mA^*$
Base-Emitter Saturation Voltage	$V_{BE(sat)}$	-1.8		-1.8		V	$I_C = 1A, I_B = 10mA^*$
Base-Emitter Turn-On Voltage	$V_{BE(on)}$	-1.7		-1.7		V	$I_C = 1A, V_{CE} = -5V^*$

查询ZTX704供应商



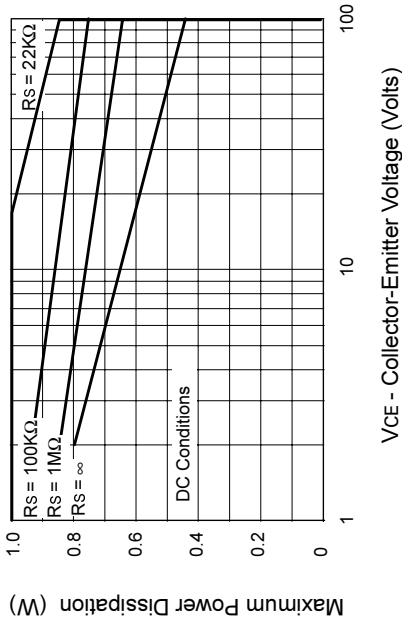
捷多邦, 专业PCB打样工厂, 24小时加急出货

ZTX704
ZTX705

ELECTRICAL CHARACTERISTICS (at T_{amb} = 25°C).

PARAMETER	SYMBOL	ZTX704		ZTX705		UNIT	CONDITIONS.
		MIN.	MAX.	MIN.	MAX.		
Static Forward Current Transfer Ratio	h _{FE}	3K		3K			I _C =-10mA, V _{CE} =-5V*
		3K		3K			I _C =-100mA, V _{CE} =-5V*
		3K	30K	3K	30K		I _C =-1A, V _{CE} =-5V*
		2K		2K			I _C =-2A, V _{CE} =-5V*
Transition Frequency	f _T	160 Typical		160 Typical		MHz	I _C =-100mA, V _{CE} =-10V f=20MHz
Input Capacitance	C _{ibo}	90 Typical		90 Typical		pF	V _{EB} =-0.5V, f=1MHz
Output Capacitance	C _{obo}	15 Typical		15 Typical		pF	V _{CE} =-10V, f=1MHz
Switching Times	t _{on}	0.6 Typical		0.6 Typical		µs	I _C =-0.5A, V _{CE} =-10V I _B =I _{B2} =-0.5mA
	t _{off}	0.8 Typical		0.8 Typical		µs	

Measured under pulsed conditions. Pulse width=300µs. Duty cycle ≤2%



Voltage Derating Graph

The maximum permissible operational temperature can be obtained from this graph using the following equation

$$T_{amb(max)} = \frac{Power(max) - Power(act)}{0.0057} - 25^{\circ}C$$

T_{amb(max)}= Maximum operating ambient temperature

Power(max) = Maximum power dissipation figure, obtained from the above graph for a given V_{CE} and source resistance (R_S)

Power(actual)= Actual power dissipation in users circuit

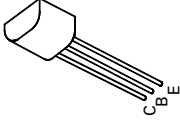
PNP SILICON PLANAR MEDIUM POWER
DARLINGTON TRANSISTORS

ISSUE 3 – MAY 94

ZTX704
ZTX705

FEATURES

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 - * P_{tot}=1 Watt
- APPLICATIONS
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E-Line

TO92 Compatible

ABSOLUTE MAXIMUM RATINGS.

PARAMETER	SYMBOL	ZTX704	ZTX705	UNIT
Collector-Base Voltage	V _{CBO}	-120	-140	V
Collector-Emitter Voltage	V _{CEO}	-100	-120	V
Emitter-Base Voltage	V _{EB0}	-10		V
Peak Pulse Current	I _{CM}	-4		A
Continuous Collector Current	I _C	-1		A
Power Dissipation at T _{amb} = 25°C derate above 25°C	P _{tot}	1	5.7	W mW/°C
Operating and Storage Temperature Range	T _J ; T _{stg}	-55 to +200		°C

ELECTRICAL CHARACTERISTICS (at T_{amb} = 25°C unless otherwise stated).

PARAMETER	SYMBOL	ZTX704		ZTX705		UNIT	CONDITIONS.
		MIN.	MAX.	MIN.	MAX.		
Collector-Base Breakdown Voltage	V _{(BR)CBO}	-120		-140		V	I _C =-100µA
Collector-Emitter Breakdown Voltage	V _{CE0(SUS)}	-100		-120		V	I _C =-10mA*
Emitter-Base Breakdown Voltage	V _{(BR)EBO}	-10		-10		V	I _E =-100µA
Collector Cut-Off Current	I _{CBO}	-0.1	-10	-0.1	-10	µA	V _{CB} =-100V
						µA	V _{CB} =-120V
						µA	V _{CB} =-100V, T _{amb} =100°C
Collector Cut-Off Current	I _{CES}	-10	-10	-10	-10	µA	V _{CB} =-120V, T _{amb} =100°C
						µA	V _{CE} =-80V
Emitter Cut-Off Current	I _{EBO}	-0.1		-0.1		µA	V _{EB} =-8V
Collector-Emitter Saturation Voltage	V _{CE(sat)}	-1.3	-2.5	-1.3	-2.5	V	I _C =-1A, I _B =-1mA*
						V	I _C =-2A, I _B =-2mA*
Base-Emitter Saturation Voltage	V _{BE(sat)}	-1.8		-1.8		V	I _C =-1A, I _B =-10mA*
Base-Emitter Turn-On Voltage	V _{BE(on)}	-1.7		-1.7		V	I _C =-1A, V _{CE} =-5V*

ZTX704
ZTX705

TYPICAL CHARACTERISTICS

